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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

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FDMS037N08B

N-Channel PowerTrench® MOSFET

75 V, 100 A, 3.7 mΩ



Features

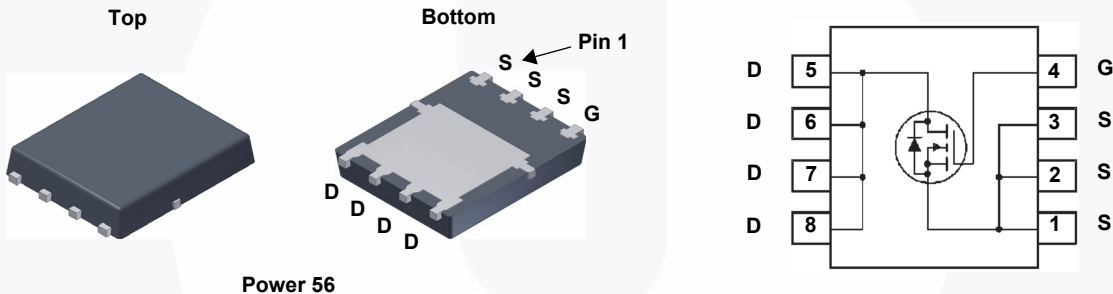
- $R_{DS(on)} = 3.01 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$
- Low FOM $R_{DS(on)} * Q_G$
- Low Reverse Recovery Charge, $Q_{rr} = 80 \text{ nC}$
- Soft Reverse Recovery Body Diode
- Enables Highly Efficiency in Synchronous Rectification
- Fast Switching Speed
- 100% UIL Tested
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection circuit
- DC Motor Drives and Uninterruptible Power Supplies



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDMS037N08B	Unit
V_{DSS}	Drain to Source Voltage	75	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	100
		- Continuous ($T_C = 25^\circ\text{C}$, Silicon Limited)	128
		- Continuous ($T_A = 25^\circ\text{C}$) (Note 1a)	19.9
I_{DM}	Drain Current	- Pulsed (Note 2)	400
E_{AS}	Single Pulsed Avalanche Energy	(Note 3)	180.6
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	104.2
		($T_A = 25^\circ\text{C}$) (Note 1a)	0.83
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FDMS037N08B	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS037N08B	FDMS037N08B	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	75	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C	-	39	-	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$	-	3.01	3.7	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}$, $I_D = 50 \text{ A}$	-	108	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 37.5 \text{ V}$, $V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$	-	4550	5915	pF
C_{oss}	Output Capacitance		-	1060	1380	pF
C_{rss}	Reverse Transfer Capacitance		-	30.2	45	pF
$C_{oss(er)}$	Energy Releated Output Capacitance	$V_{DS} = 37.5 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	1702	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 37.5 \text{ V}$, $I_D = 50 \text{ A}$ $V_{GS} = 0 \text{ V}$ to 10 V	-	76.8	100	nC
Q_{gs}	Gate to Source Gate Charge		-	27.5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	17.4	-	nC
$V_{plateau}$	Gate Plateau Volatge		(Note 4)	-	5.1	-
Q_{sync}	Total Gate Charge Sync.	$V_{DS} = 0 \text{ V}$, $I_D = 50 \text{ A}$	-	66.3	-	nC
Q_{oss}	Output Charge	$V_{DS} = 37.5 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	74.6	-	nC
ESR	Equivalent Series Resistance	$f = 1 \text{ MHz}$	-	1.28	-	Ω

Switching Characteristics

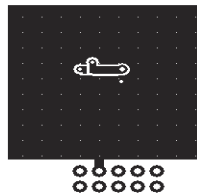
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 37.5 \text{ V}$, $I_D = 50 \text{ A}$ $V_{GS} = 10 \text{ V}$, $R_G = 4.7 \Omega$	-	34.9	80	ns
t_r	Turn-On Rise Time		-	20.1	50	ns
$t_{d(off)}$	Turn-Off Delay Time		-	55.3	120	ns
t_f	Turn-Off Fall Time		(Note 4)	-	19.4	49

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	100	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	400	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_{SD} = 50 \text{ A}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$, $I_{SD} = 50 \text{ A}$	-	66.8	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100 \text{ A}/\mu\text{s}$	-	84	-	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5 \text{ in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Repetitive rating: pulse-width limited by maximum junction temperature.
3. $L = 0.3 \text{ mH}$, $I_{AS} = 34.7 \text{ A}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

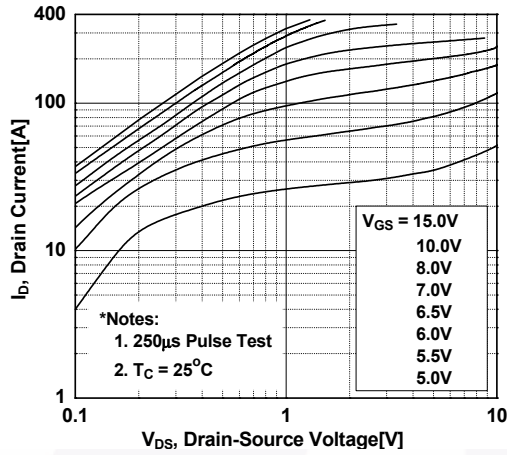


Figure 2. Transfer Characteristics

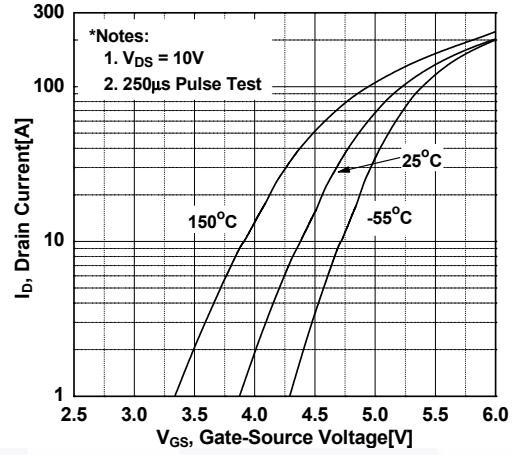


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

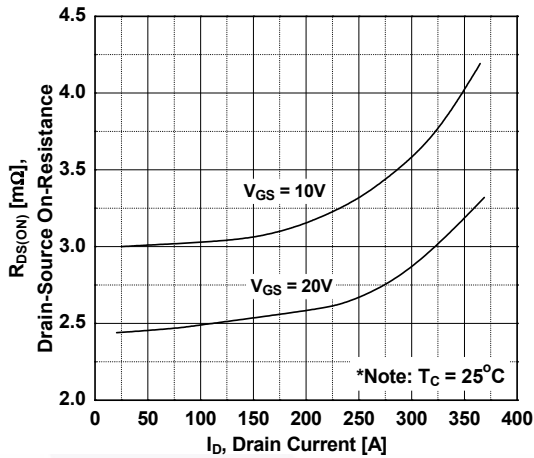


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

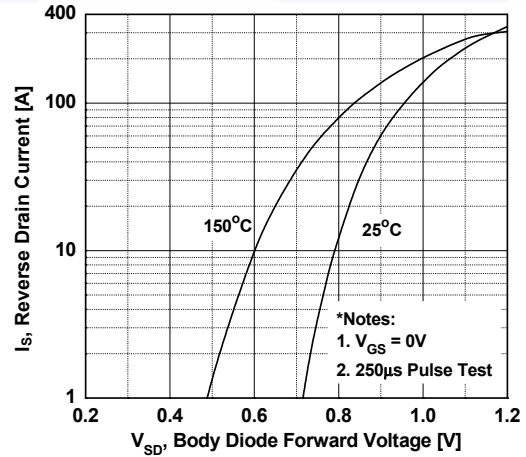


Figure 5. Capacitance Characteristics

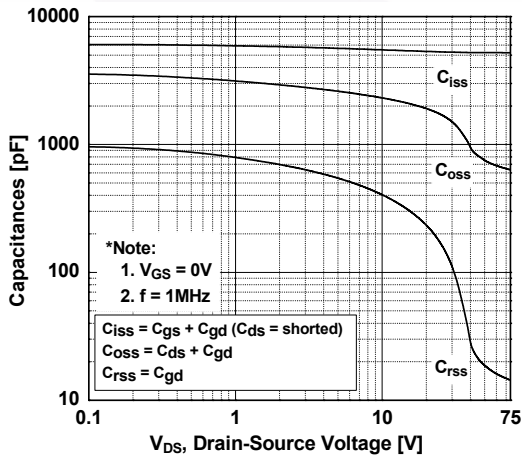
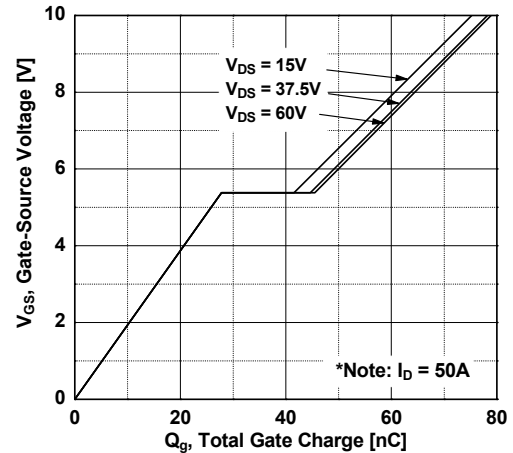


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

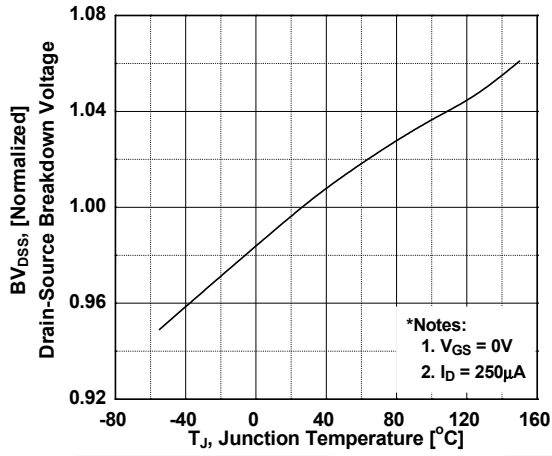


Figure 8. On-Resistance Variation vs. Temperature

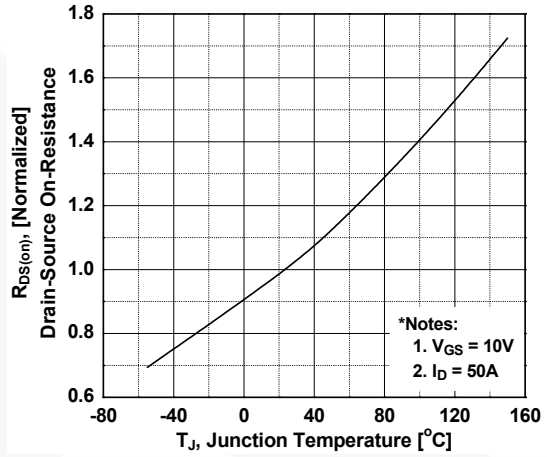


Figure 9. Maximum Safe Operating Area

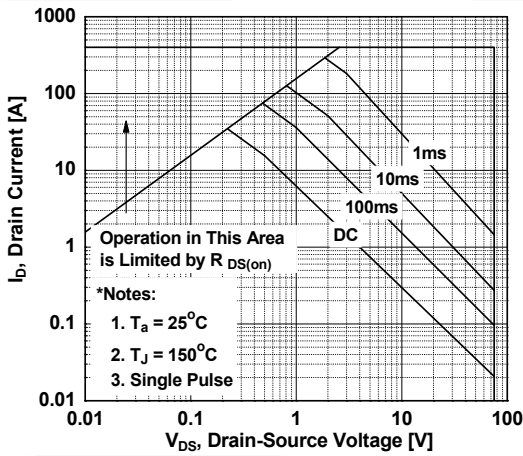


Figure 10. Maximum Drain Current vs. Case Temperature

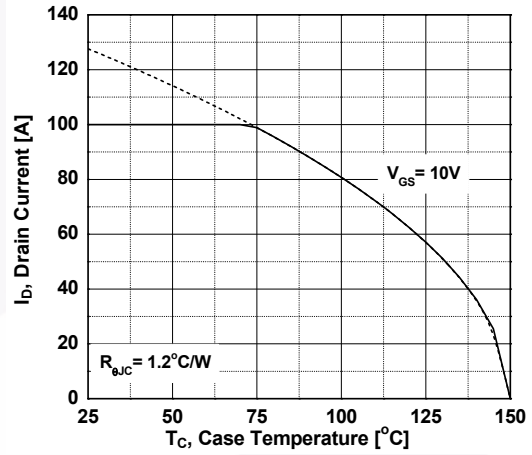


Figure 11. E_oss vs. Drain to Source Voltage

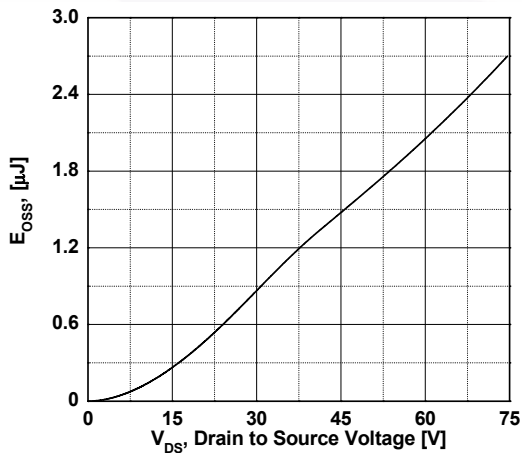
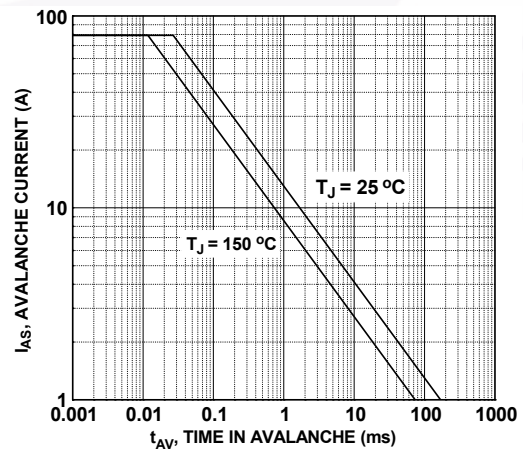


Figure 12. Unclamped Inductive Switching Capability



Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve

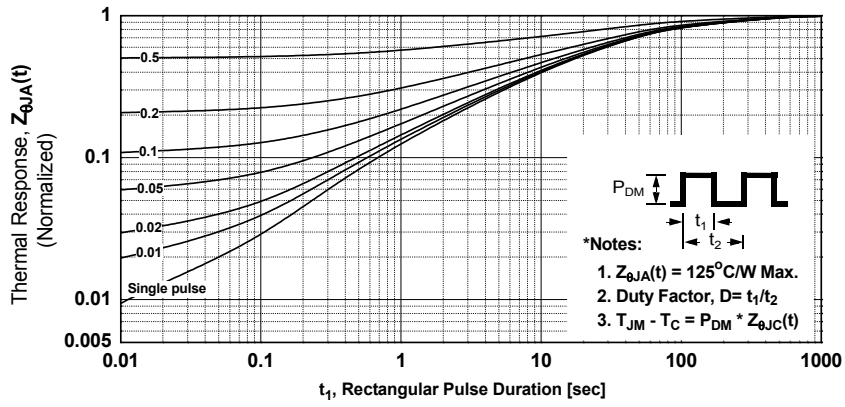


Figure 14. Gate Charge Test Circuit & Waveform

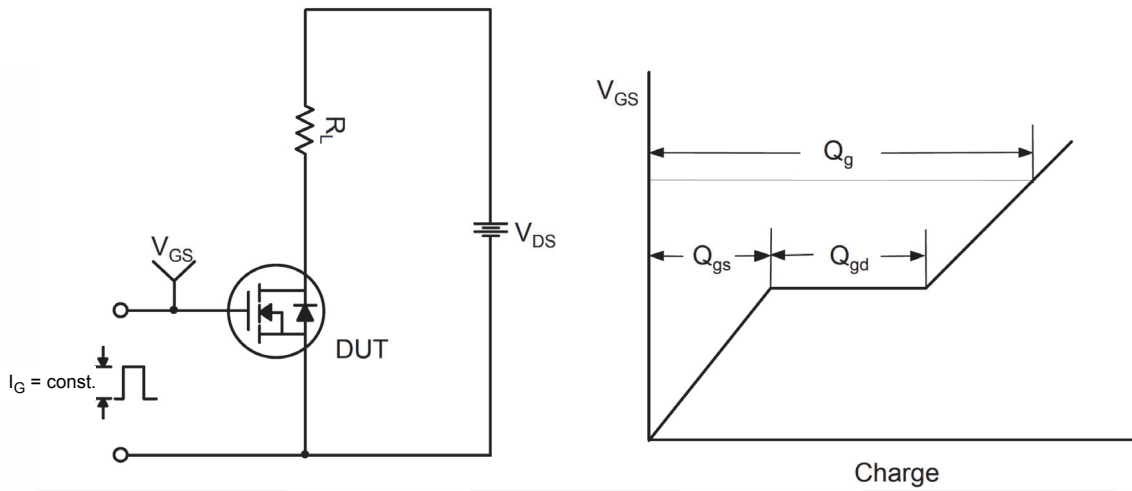


Figure 15. Resistive Switching Test Circuit & Waveforms

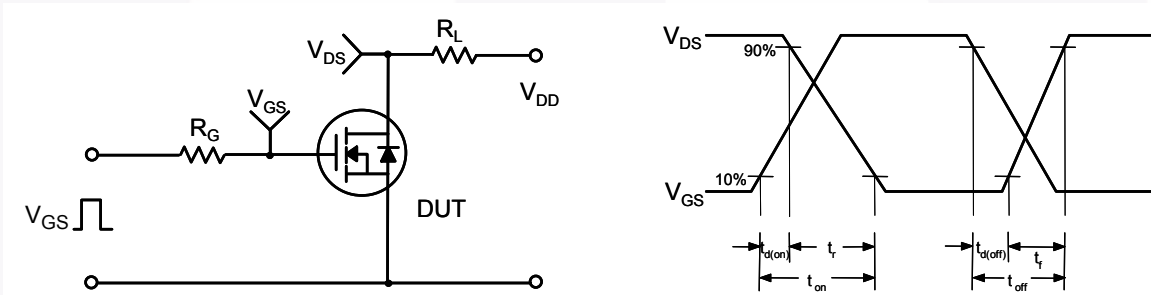


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

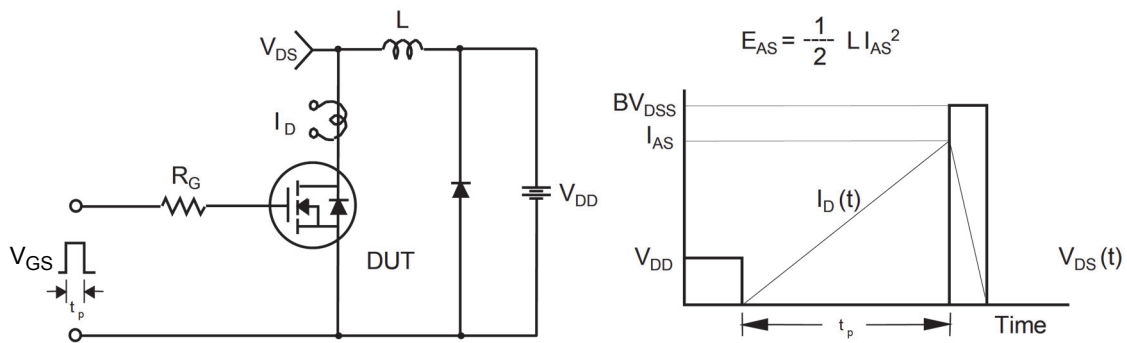


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

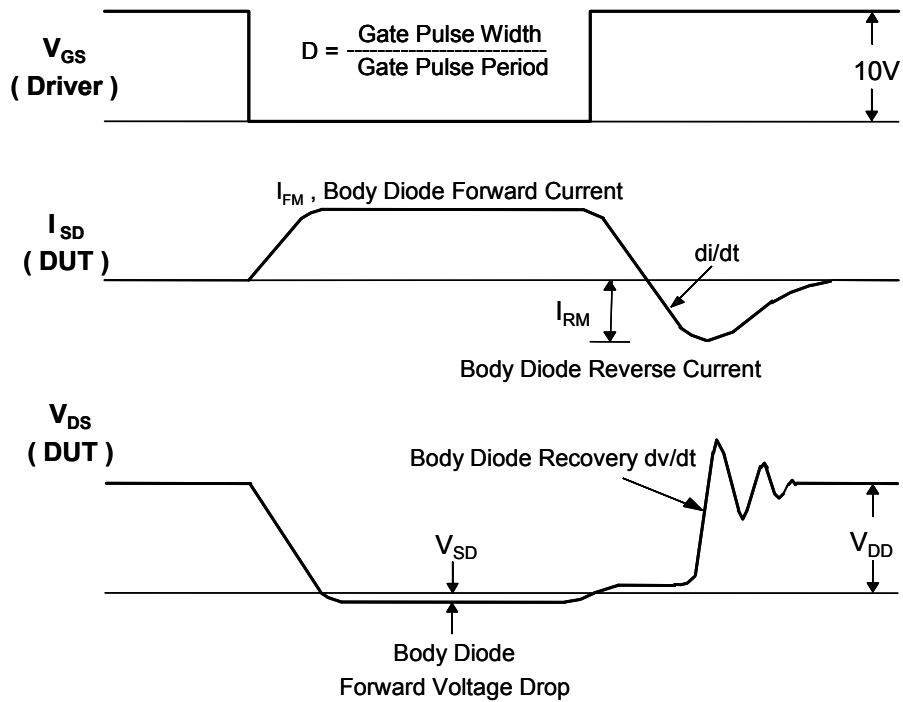
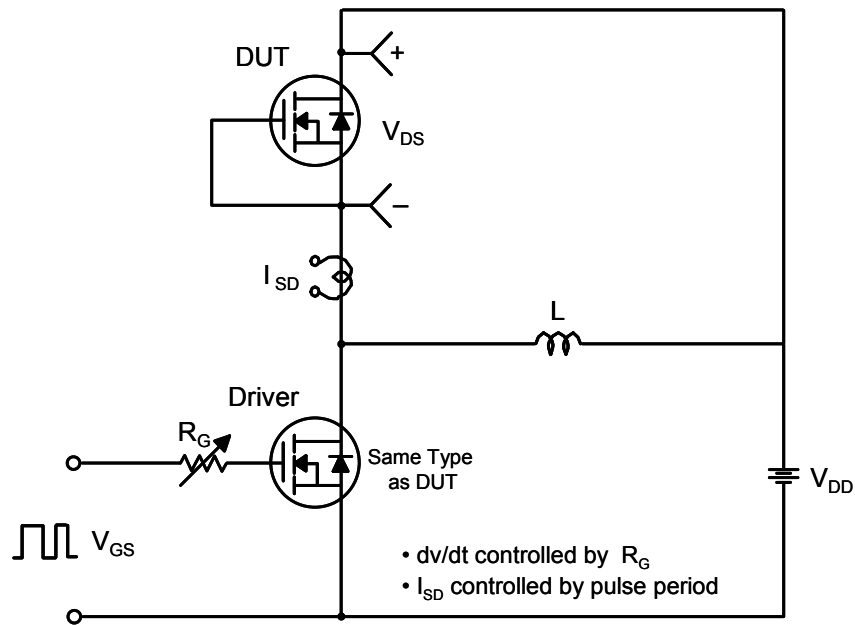
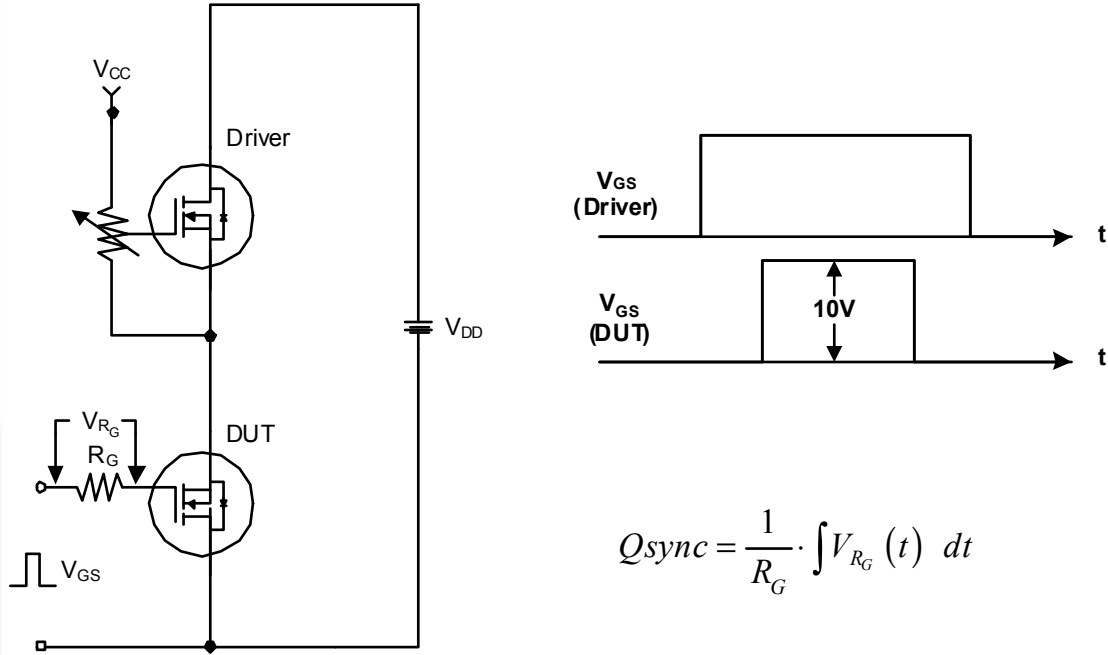
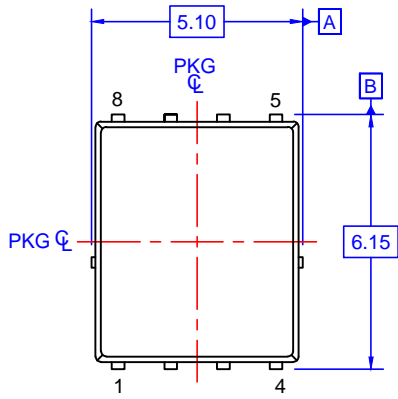


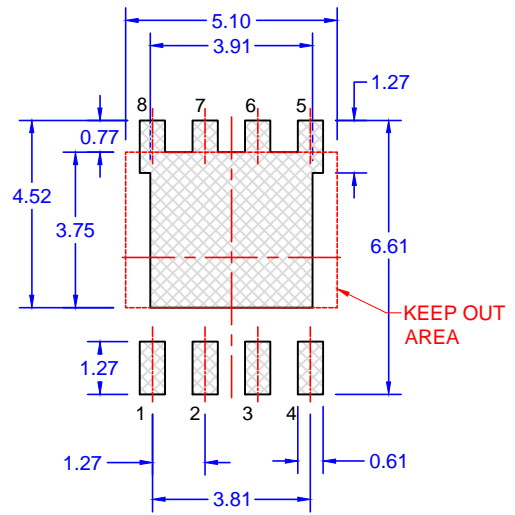
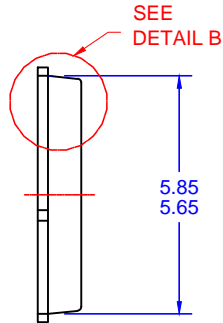
Figure 18. Total Gate Charge Q_{sync} . Test Circuit & Waveforms



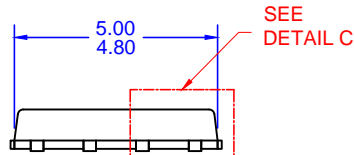
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



TOP VIEW

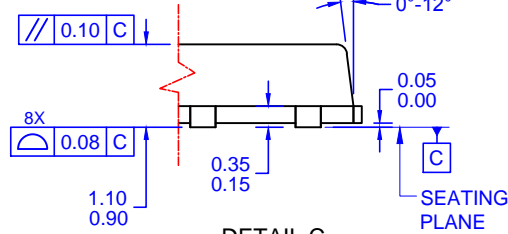


LAND PATTERN RECOMMENDATION

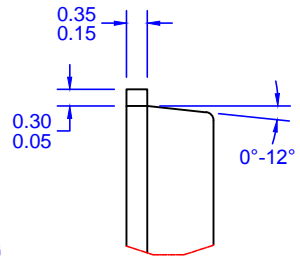


SIDE VIEW

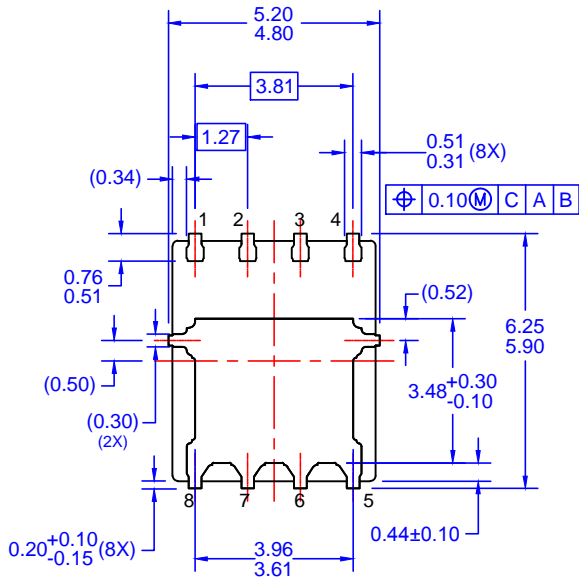
OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA.
- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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